### 1. OVERVIEW

The CF7060xAS/WF7060xAS series are differential output oscillator ICs of the HCSL output type. They support 125degree operation and wide range of output frequencies.

They are suitable for high frequency applications such as high speed communication devices.

They use an oscillation circuit suitable for small crystal elements, therefore suitable for a small package oscillation module.

### 2. FEATURES

- Operating supply voltage:
- Operating temperature:
- Recommended oscillation frequency  $(f_0)$ :
- Output frequency  $(f_{OUT})$ :
- Oscillator capacitances:
- Output level:
- Standby function:

■ Oscillation detection circuit built-in

 $\begin{array}{ll} 1.71 \mbox{ to } 1.89 \mbox{ V} \\ -40 \mbox{ °C to } +125 \mbox{ °C } \\ 3 \mbox{ rd overtone frequency } 100 \mbox{ MHz to } 175 \mbox{ MHz } \\ F \mbox{ undamental frequency } 100 \mbox{ MHz to } 175 \mbox{ MHz } \\ f_0 \\ C_G, \mbox{ C}_D \mbox{ built-in } \\ \mbox{ HCSL } \\ Oscillator \mbox{ stops, Hi-Z outputs, } \\ power \mbox{ saving pull-up resistor built-in (OE output) } \end{array}$ 

# 3. BLOCK DIAGRAM



## 4. PAD LAYOUT

- (1) Chip size<sup>\*1:</sup> X=0.75mm, Y=0.65mm
- (2) Rear surface potential: Vss level
- (3) Pad size: No. 1,6,7:100μm × 80μm
  No. 2,3,4,5:80μm × 80μm
- (4) Chip dimensions
  - \*1. Chip size is measured between scribe line centers.



No. Х Y Name 1 -271 -231 VDD 2 -77 -231 XIN 3 115 -231 XOUT 4 281 -231 OE VSS 5 281 231 6 -93 231 OUTN 7 -271 231 OUT

Pad Coordinates (Origin in chip center), Unit: [µm]

### 5. PAD DESCRIPTION

Number	Name	I/O <sup>*1</sup>	Function
1	VDD	-	(+) Supply voltage
2	XIN	Ι	Oscillator connections
3	XOUT	0	Oscillator connections
4	OE	Ι	Output enable. Outputs are disabled when OE is V <sub>SS</sub> level. Disabled state: Oscillator stopped, Hi-Z outputs
5	VSS	-	(-) Supply voltage
6	OUTN	0	output (inverting output) Disabled state: Hi-Z
7	OUT	0	output Disabled state: Hi-Z

\*1. I : Input, O : Output

## 6. VERSION LINEUP



Output level
 Output freqency
 Oscillation frequency range

(1) Version name 1<sup>st</sup> character (oscillation frequency range)

Version	Oscillation mode	Recommended C0 value (nF)*1	Oscil capac (pF	llator itance <sup>(</sup> )* <sup>2</sup>	Oscillation frequency (reference values)	
		( <b>pr</b> )	CG	CD		
D	3rd overtone Fundamental	1.0~ 2.0*3	4	11	100~135	
Ε	3rd overtone Fundamental	$1.0 \sim 2.0^{*3}$	4	9	135~175	

\*1. It is the normal recommended range where the value of mention was based on an oscillation circuitry in the upper section.

\*2. Values do not include parasitic capacitance.

\*3. This version has a C0 cancel circuit to ensure negative resistance at high frequency. A self-oscillation becomes easy to happen coldly, so please be careful and do initial evaluation.

\* Version, recommended C0 value and oscillation frequency are provisional.

(2) Version name  $2^{nd}$  character (output frequency)

Version	Output frequency (f <sub>OUT</sub> )
А	$f_0$

(3) Version name 3<sup>rd</sup> character (Output level)

Version S	Oscillation
version	frequency range
S	HCSL

.....

## 7. ABSOLUTE MAXIMUM RATINGS

					$V_{SS}=0V$
Parameter	Symbol	Conditions	Rating	Unit	Notes
Supply voltage range	V <sub>DD</sub>	Between VDD and VSS	-0.3 ~ +4.5	V	*1
Input voltage range1 V <sub>IN1</sub>		OE	$-0.3 \sim V_{DD} + 0.3$	V	*1,*2
Input voltage range2	V <sub>IN2</sub>	XIN	-0.3 ~ +2.5	V	*1,*2
Output voltage range1	V <sub>OUT1</sub>	OUT,OUTN	-0.3 ~ V <sub>DD</sub> +0.3	V	*1、*2
Output voltage range2 V		XOUT	-0.3 ~ +2.5	V	*1,*2
Junction temperature T <sub>j</sub>			+150	°C	*3
Storage temperature range	T <sub>STG</sub>	Chip, wafer form	-55 ~ +150	°C	*4

\*1. Parameters must not exceed ratings, not even momentarily. If the rating is exceeded, it may affect the electrical characteristics and reliability.

\*2. V<sub>DD</sub> indicates the operating supply voltage in "8. RECOMMENDED OPERATING CONDITIONS."

\*3. Do not exceed ratings. If a rating is exceeded, there is a risk of deterioration in characteristics and decrease in reliability.

\*4. When stored separately in Nitrogen or vacuum atmosphere.

## 8. RECOMMENDED OPERATING CONDITIONS

					V	ss=0V
Parameter	Symbol	Conditions	MIN	ТҮР	MAX	Unit
Oscillation frequency <sup>*1</sup>	$f_0$		100	-	175	MHz
Output frequency	f <sub>OUT</sub>		100	-	175	MHz
Operating supply voltage	V <sub>DD</sub>	VDD and VSS <sup>*2</sup>	1.71	-	1.89	V
Input voltage	V <sub>IN</sub>	OE	0		V <sub>DD</sub>	V
		XIN	0	-	1.89	V
Operating temperature	Ta		-40		+125	°C
Output load resistance	R <sub>L</sub>	Between OUT(Rs) and $V_{SS}$ Between OUTN(Rs) and $V_{SS}$	49.5	50	50.5	Ω
Damping resistance <sup>*3</sup>	R <sub>S</sub>	Between OUT and $R_L$ Between OUTN and $R_L$	-	0	-	Ω

\*1. The oscillation frequency range is a target based on evaluation results for the crystal element used for NPC characteristics verification, and does not represent a guarantee of the oscillation frequency band. The oscillation characteristics can vary significantly depending on the characteristics and mounting conditions of the crystal. Accordingly, oscillation characteristics should be thoroughly evaluated for each crystal.

\*2. For stable device operation, connect a 0.01µF or larger ceramic chip capacitor between VDD and VSS, mounted close (within approximately 3mm) to the chip. Also, use the thickest wiring possible between the IC and capacitor.

\*3. This product is designed for low voltage operation. If a damping resistor is connected to the product, the operating range of the output circuit will be narrowed. Therefore, the voltage amplitude of the output circuit will not meet the specifications.

\* Since it may influence the reliability if it is used out of the recommended operating conditions range, this product should be used within this range.

## 9. ELECTRICAL CHARACTERISTICS

### 9.1. DC Characteristics

Measurement circuits 1 to 3 in "Conditions" are shown in "12. MEASUREMENT CIRCUITS."

Parameter	Symbol	Conditions		MIN	ТҮР	MAX	Unit
Current concurrention	I <sub>DDD</sub>	Measurement circuit 1 OE=Open f <sub>0</sub> =125MHz, DASver.	V <sub>DD</sub> =1.8V	_	34	42	mA
Current consumption	$I_{\text{DDE}}$	Measurement circuit 1 OE=Open f <sub>0</sub> =156MHz, EASver.	V <sub>DD</sub> =1.8V	-	36	46	mA
Standby current	I <sub>STB</sub>	Measurement circuit 1, OE=	= V <sub>SS</sub>	-	-	30	μA
High-level output voltage	V <sub>OH</sub>	Measurement circuit 2 OUT/OUTN		0.55	-	1.0	V
Low-level output voltage	V <sub>OL</sub>	Measurement circuit 2, OU	Γ/Ουτη	-0.15	-	0.15	V
High-level input voltage	$V_{IH}$	Measurement circuit 1, OE		$0.7 V_{DD}$	-	-	V
Low-level input voltage	V <sub>IL</sub>	Measurement circuit 1, OE		-	-	$0.3V_{\text{DD}}$	V
OE pull-up	R <sub>PU1</sub>	Measurement circuit 1		0.5	1	2	MΩ
resistance	$R_{PU2}$	Measurement circuit 1		30	70	150	kΩ
Oscillator feedback resistance (DAS ver.)	R <sub>FD</sub>	Design value		1.8	2.3	2.9	kΩ
Oscillator feedback resistance (EASver.)	R <sub>FE</sub>	Design value		1.8	2.3	2.9	kΩ
Oscillator capacitance	C <sub>GD</sub>	Design value,		3.2	4.0	4.8	ΞĒ
(DAS ver.)	C <sub>DD</sub>	Excludes parasitic capacitance	e	8.8	11.0	13.2	рг
Oscillator capacitance	C <sub>GE</sub>	Design value,		3.2	4.0	4.8	ъĘ
Standby currentHigh-level output voltageLow-level output voltageHigh-level input voltageLow-level input voltageDow-level input voltageOE pull-up resistanceOscillator feedback resistance (DAS ver.)Oscillator capacitance (DAS ver.)Oscillator capacitance (DAS ver.)Oscillator capacitance (DAS ver.)Oscillator capacitance (DAS ver.)Oscillator capacitance (DAS ver.)Oscillator capacitance (EAS ver.)	C <sub>DE</sub>	Excludes parasitic capacitance	e	7.2	9.0	10.8	рг

 $V_{DD}$ =1.71 to 1.89V,  $V_{SS}$ =0V,  $T_a$ =-40 to +125°C unless otherwise noted

### 9.2. AC Characteristics

Measurement circuits 4 and 5 in "Conditions" are shown in "12. MEASUREMENT CIRCUITS." The conditions for each parameter assume the timing shown in "9.3 TIMING DIAGRAM."

Parameter	Symbol	Conditions		MIN	ТҮР	MAX	Unit
Output duty cycle	Duty	Measurement circuit 3 Measured at 0V crossover differential output signal	point of	45	-	55	%
Output amplitude	V <sub>OPP</sub>	Measurement circuit 3 Single-ended output signal		0.4	-	-	V
Output rise slew rate *2	t <sub>SRrise</sub>	Measurement circuit 3 differential output signal Measured at 0V crossover point $\pm 150$ mV	C <sub>L</sub> =2pF <sup>*1</sup>	0.6	-	5	V/ns
Output fall slew rate <sup>*2</sup>	t <sub>SRfall</sub>	Measurement circuit 3 differential output signal Measured at 0V crossover point $\pm 150$ mV	$C_L=2pF^{*1}$	0.6	-	5	V/ns
Output disable time <sup>*2</sup>	t <sub>OD</sub>	Measurement circuit 4 Time measured $OE=V_{IL}$ (fallin outputs going Hi-Z (see timing details)	g edge) and diagram for	_	_	200	ns

 $V_{DD}$ =1.71 to 1.89V,  $V_{SS}$ =0V,  $T_a$ =-40 to +125°C unless otherwise noted

\*1. C<sub>L</sub> contains the parasitic capacitance, such as evaluation board, package.

\*2. Since shipping inspection is not possible, it is guaranteed by characterization.

\* The ratings above are values obtained by measurements using an NPC evaluation standard crystal element, standard testing jig, and evaluation package.

Ratings may have wide tolerances due to crystal element characteristics, evaluation jig, and package parasitic capacitance, so thorough evaluation is recommended.

## 9.3. Timing Diagram

The timing diagram applies to the "Conditions" in the table in "9.2. AC Characteristics."



\*1. The time, after OE falling edge and the output disable time  $(t_{OD})$  has elapsed, taken until the outputs become high impedance (Hi-Z).

Figure 9. HCSL Timing diagram

## 10. REFERENCE CHARACTERISTICS (Typical 7060 Characteristics)

The following characteristics assume the use of the following crystal element. The characteristics will vary depending on the crystal used and the measurement conditions.



\* Crystal oscillator element

Parameter	f <sub>0</sub> =100MHz	f <sub>0</sub> =155.52MHz
C0(pF)	1.8	1.5
$R1(\Omega)$	7.9	11
Oscillation mode	Fundamental	Fundamental



7060DAS,  $f_{OUT}$ =100MHz,  $T_a$ =25°C



7060EAS, f<sub>OUT</sub>=155.52MHz, T<sub>a</sub>=25°C



#### 10.3. Frequency Deviation vs. Voltage



7060DAS, f<sub>OUT</sub>=100MHz, T<sub>a</sub>=25°C, 1.8V std.





7060EAS, f<sub>OUT</sub>=155.52MHz, T<sub>a</sub>=25°C, 1.8V std.

### 10.4. Drive Level

7060DAS, f <sub>OUT</sub> =100MHz, T <sub>a</sub> =25°C			
	VDD[V]	Drive level [uW]	
	1.8	94.6	

7060EAS,	f <sub>OUT</sub> =155.52MHz,	Ta	=25°	С

$V_{DD}[V]$	Drive level [uW]	
1.8	131.3	

### 10.5. Phase Noise



 $T_a=25^{\circ}C$ 

## 10.6. Output Waveforms

measuring instrument : oscilloscope 80604B(Agilent)



7060DAS,  $f_{OUT}$ =100MHz,  $V_{DD}$ =1.8V,  $T_a$ =25°C,  $C_L$ =2pF





### **11. FUNCTIONAL DESCRIPTION**

#### 11.1. OE Function

When OE goes  $V_{SS}$ , the OUT/OUTN outputs stop and become high impedance. This function is used to disable the operation of the device.

OE input	OUT/OUTN outputs	Oscillator circuit
V <sub>DD</sub> or Open	f <sub>0</sub> output	Operating
V <sub>SS</sub>	Hi-Z	Stopped

#### **11.2.** Power Saving Pull-up Resistor

The OE terminal pull-up resistance switches between  $R_{PU1}$  and  $R_{PU2}$ , depending on the input level ( $V_{DD}$  or  $V_{SS}$ ).

When the OE terminal is held  $V_{SS}$ , the built-in OE terminal pull-up resistance increases ( $R_{PU1}$ ), reducing the current consumed by the pull-up resistance when the outputs are disabled.

When the device is operating with the OE terminal  $V_{DD}$  or open circuit, the pull-up resistance decreases ( $R_{PU2}$ ), reducing internal susceptibility to the effects of external noise. The OE terminal is held  $V_{DD}$  internally to prevent problems that might otherwise cause the outputs to stop abruptly.

#### **11.3.** Oscillation Detection Function

The IC has a built-in oscillation detection circuit.

The oscillation detection circuit disables the output circuit when the oscillator starts until the oscillation becomes stable. This function limits the danger of unstable oscillation when the oscillator starts after power is first applied or the output is enabled.

#### 11.4. C0 cancellation circuit

Oscillation circuit with a built-in C0 cancellation circuit provides a fixed compensation amount to cancel the effect of the crystal C0. It reduces the C0 parameter in the equivalent circuit, reducing the shallow negative resistance for increasing values of C0.

This cancellation circuit makes it easier to maintain the oscillation margin.

### **12. MEASUREMENT CIRCUITS**

These measurement circuits are used for DC and AC characteristics evaluation.

\*\*\*\*\* Cautions for output waveform \*\*\*\*\*

To obtain good waveform characteristics, place a ceramic chip capacitor of 0.01  $\mu$ F (or more) between the VDD and VSS pins of the IC (within about 3 mm).

### 12.1. HCSL

• Measurement circuit 1 Measurement parameters: I<sub>DD</sub>, I<sub>STB</sub>, V<sub>IH</sub>, V<sub>IL</sub>, R<sub>PU1</sub>, R<sub>PU2</sub>



fig12-1. Measurement circuit 1

• Measurement circuit 2 Measurement parameters: V<sub>OH</sub>, V<sub>OL</sub>



• Measurement circuit 3 Measurement parameters: Duty, V<sub>OPP</sub>, t<sub>SRrise</sub>, t<sub>SRfall</sub>



fig12-3. Measurement circuit 3

• Measurement circuit 4 Measurement parameters: t<sub>OD</sub>



fig12-4. Measurement circuit 4

## **13. WAFER SURFACE DIAGRAM**

Wafer size:	$200$ mm $\pm 0.5$ mm
Scribe line width:	60µm



### 14. CROSS SECTION STRUCTURE



\*Film thicknesses of mention is a value in the designs as above and is not the actual value in the chip.

### 14.2. Seal Ring and Scribe Line Cross Section Structure



\*Widths of mention is a value in the designs as above and is not the actual value in the chip.

<Notes on UBM formation>

In UBM (Under Bump Metal) formation to the mounting pad electrode by electroless plating, UBM is similarly formed on the scribe line TEG and the metal exposed part of the accessory. So mask process covering the scribe line is required to prevent these effects.

### **15. USAGE AND PRECAUTIONS**

This product is designed and manufactured to the generally accepted standards of reliability as expected for use in general electronic and electrical equipment, such as personal equipment, machine tools, and measurement equipment. This product is not designed and manufactured to be used in any other special equipment requiring extremely high level of reliability and safety, such as aerospace equipment, nuclear power control equipment, medical equipment, transportation equipment, disaster prevention equipment, security equipment.

If you wish to use this product in equipment requiring extremely high level of reliability, please contact our sales department or representative in advance.

In the event that this product is used in such equipment, please take scrupulous care and apply fail-safe techniques including redundancy and malfunction prevention in order to prevent damage to life, health, property, or infrastructure etc. in case there is some malfunction in the product.

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